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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I ² C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	19
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 8x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	24-LSSOP (0.220", 5.60mm Width)
Supplier Device Package	24-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f213g2cdsp-w4

1.2 Product List

Table 1.3 lists Product List for R8C/3GC Group, and Figure 1.1 shows a Part Number, Memory Size, and Package of R8C/3GC Group.

Table 1.3 Product List for R8C/3GC Group

Current of Oct 2010

Part No.	ROM Capacity		RAM Capacity	Package Type	Remarks
	Program ROM	Data flash			
R5F213G2CNNP	8 Kbytes	1 Kbyte × 4	1 Kbyte	PWQN0024KC-A	N version
R5F213G4CNNP	16 Kbytes	1 Kbyte × 4	1.5 Kbytes	PWQN0024KC-A	
R5F213G5CNNP	24 Kbytes	1 Kbyte × 4	2 Kbytes	PWQN0024KC-A	
R5F213G6CNNP	32 Kbytes	1 Kbyte × 4	2.5 Kbytes	PWQN0024KC-A	
R5F213G1CNSP	4 Kbytes	1 Kbyte × 4	512 byte	PLSP0024JB-A	
R5F213G2CNSP	8 Kbytes	1 Kbyte × 4	1 Kbyte	PLSP0024JB-A	
R5F213G4CNSP	16 Kbytes	1 Kbyte × 4	1.5 Kbytes	PLSP0024JB-A	
R5F213G5CNSP	24 Kbytes	1 Kbyte × 4	2 Kbytes	PLSP0024JB-A	
R5F213G6CNSP	32 Kbytes	1 Kbyte × 4	2.5 Kbytes	PLSP0024JB-A	D version
R5F213G1CDSP	4 Kbytes	1 Kbyte × 4	512 byte	PLSP0024JB-A	
R5F213G2CDSP	8 Kbytes	1 Kbyte × 4	1 Kbyte	PLSP0024JB-A	
R5F213G4CDSP	16 Kbytes	1 Kbyte × 4	1.5 Kbytes	PLSP0024JB-A	
R5F213G5CDSP	24 Kbytes	1 Kbyte × 4	2 Kbytes	PLSP0024JB-A	
R5F213G6CDSP	32 Kbytes	1 Kbyte × 4	2.5 Kbytes	PLSP0024JB-A	

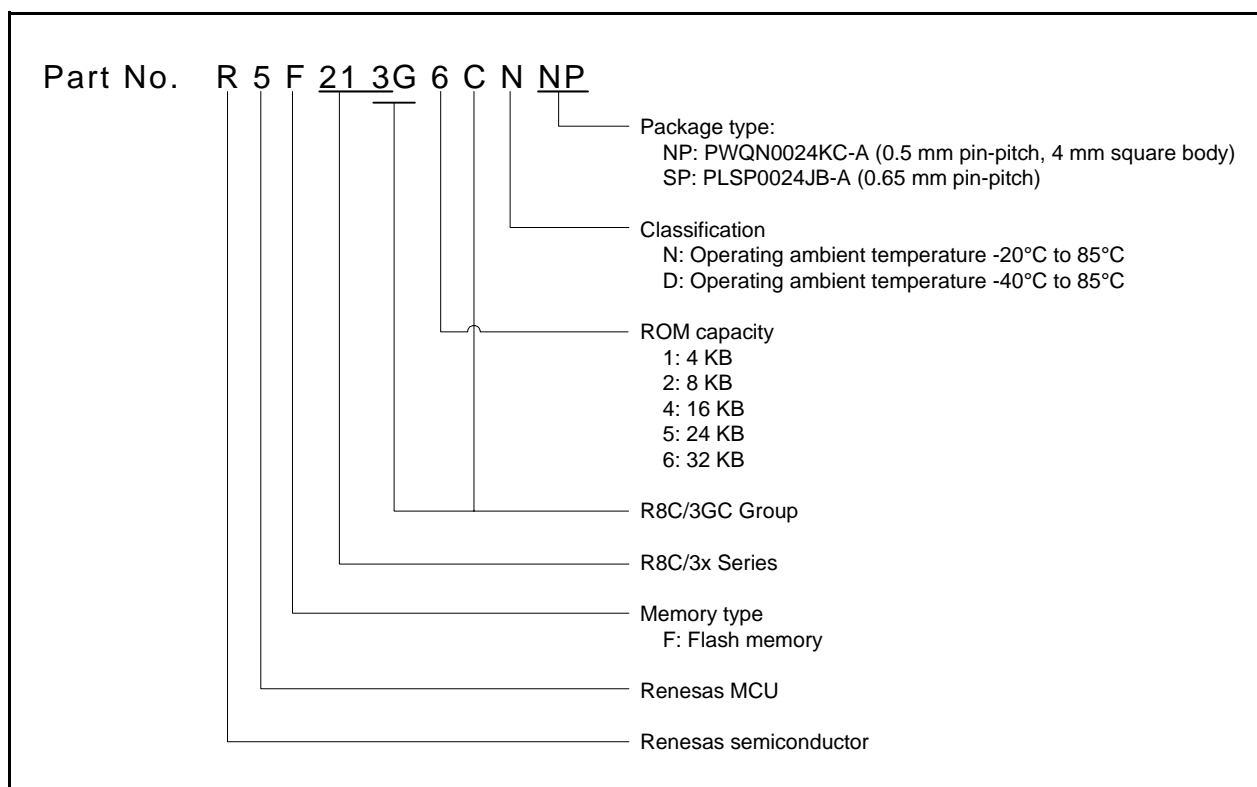


Figure 1.1 Part Number, Memory Size, and Package of R8C/3GC Group

1.3 Block Diagram

Figure 1.2 shows a Block Diagram.

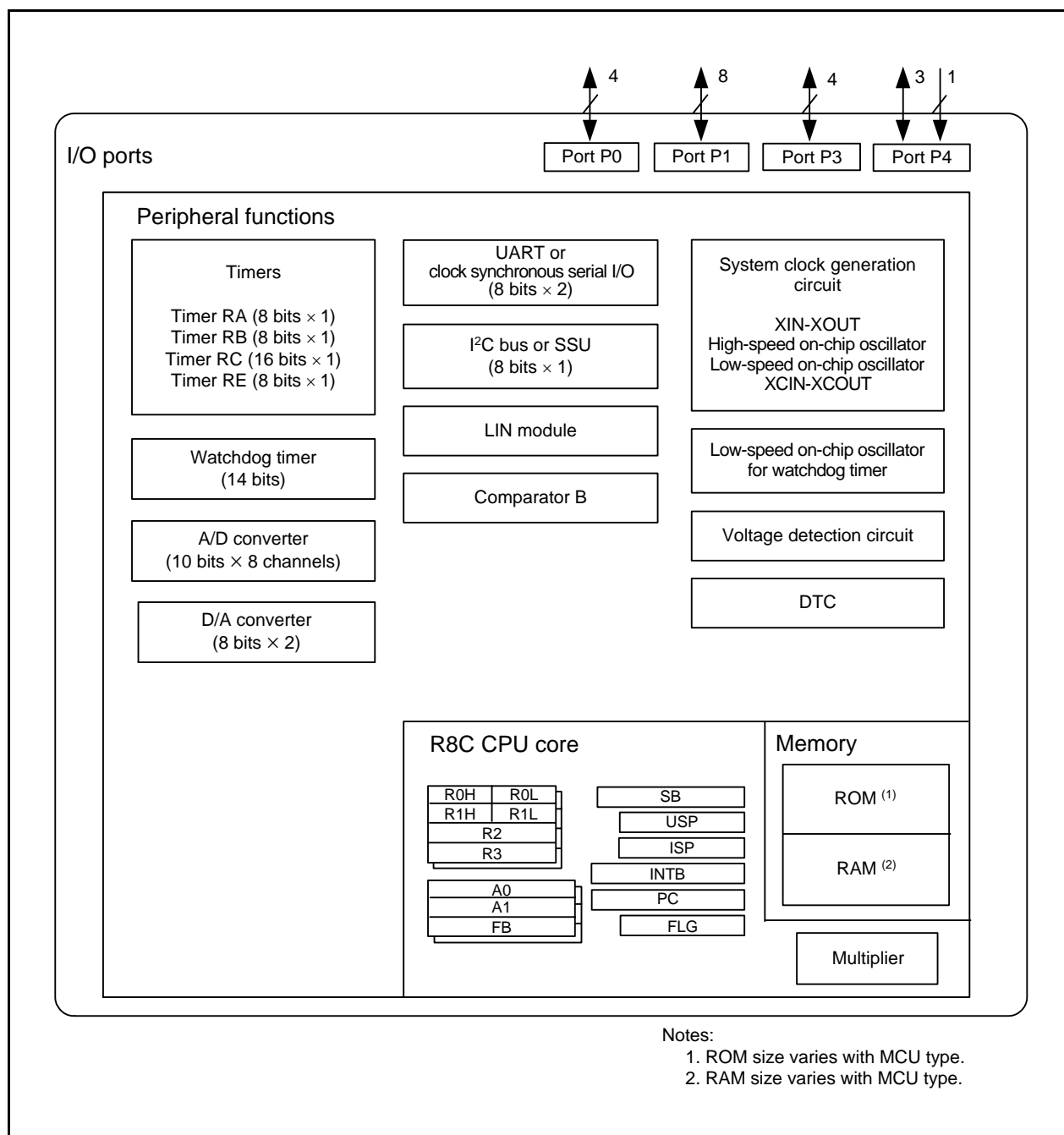


Figure 1.2 Block Diagram

Figure 1.4 shows Pin Assignment (Top View) of PLSP0024JB-A Package. Table 1.5 outlines the Pin Name Information by Pin Number.

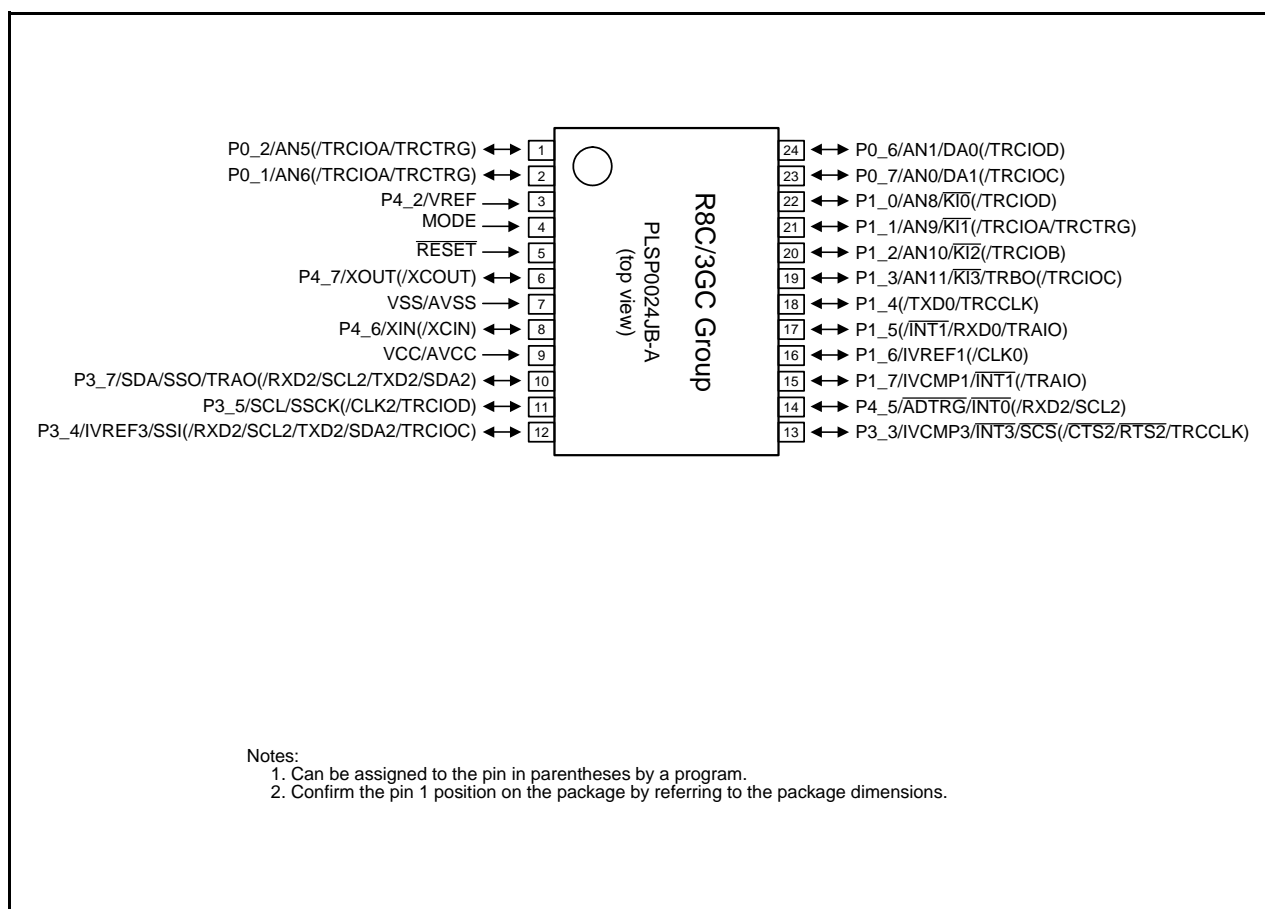


Figure 1.4 Pin Assignment (Top View) of PLSP0024JB-A Package

2. Central Processing Unit (CPU)

Figure 2.1 shows the CPU Registers. The CPU contains 13 registers. R0, R1, R2, R3, A0, A1, and FB configure a register bank. There are two sets of register bank.

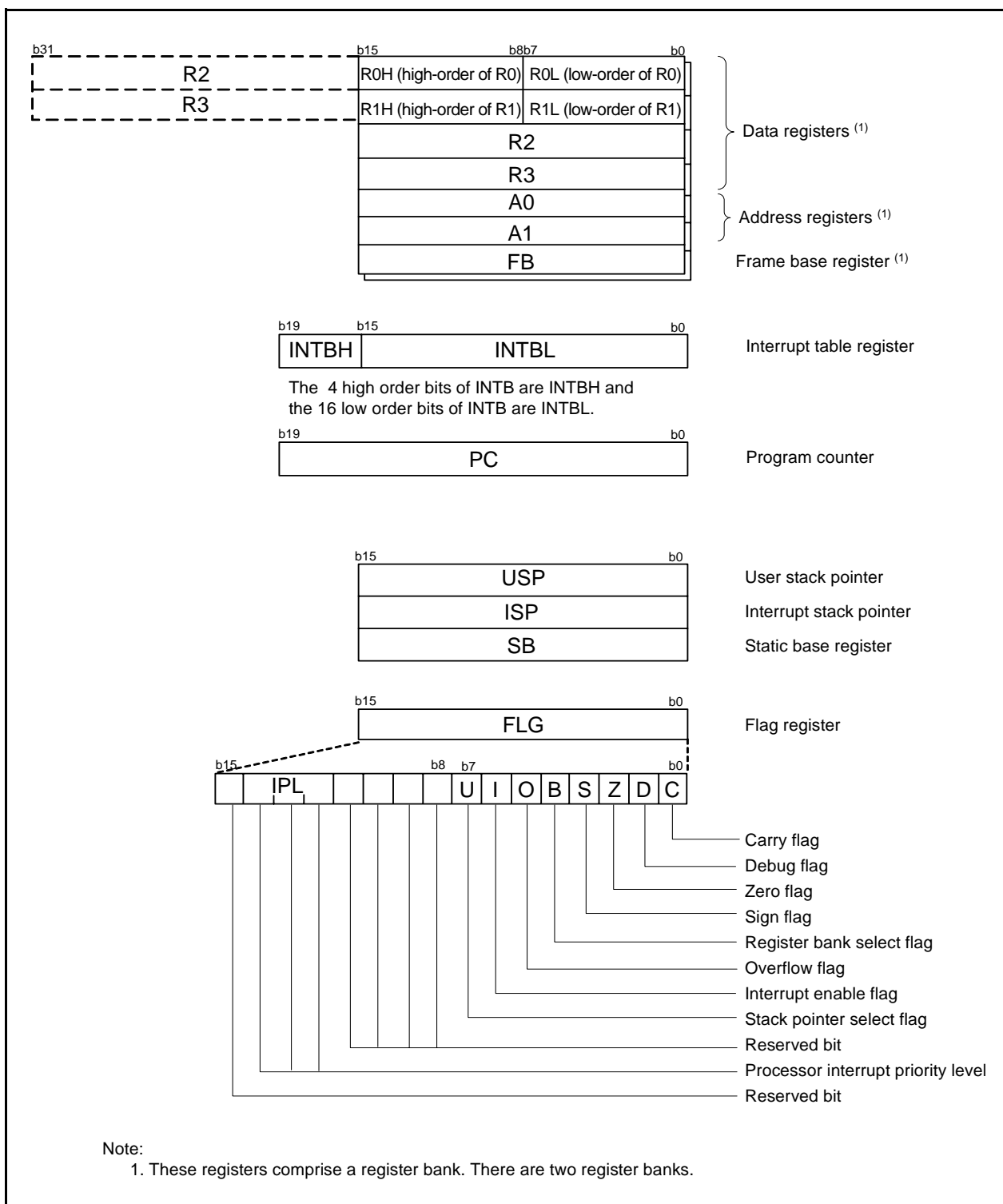


Figure 2.1 CPU Registers

2.8.7 Interrupt Enable Flag (I)

The I flag enables maskable interrupts.

Interrupts are disabled when the I flag is set to 0, and are enabled when the I flag is set to 1. The I flag is set to 0 when an interrupt request is acknowledged.

2.8.8 Stack Pointer Select Flag (U)

ISP is selected when the U flag is set to 0; USP is selected when the U flag is set to 1.

The U flag is set to 0 when a hardware interrupt request is acknowledged or the INT instruction of software interrupt numbers 0 to 31 is executed.

2.8.9 Processor Interrupt Priority Level (IPL)

IPL is 3 bits wide and assigns processor interrupt priority levels from level 0 to level 7.

If a requested interrupt has higher priority than IPL, the interrupt is enabled.

2.8.10 Reserved Bit

If necessary, set to 0. When read, the content is undefined.

Table 4.3 SFR Information (3) (1)

Address	Register	Symbol	After Reset
0080h	DTC Activation Control Register	DTCTL	00h
0081h			
0082h			
0083h			
0084h			
0085h			
0086h			
0087h			
0088h	DTC Activation Enable Register 0	DTCEN0	00h
0089h	DTC Activation Enable Register 1	DTCEN1	00h
008Ah	DTC Activation Enable Register 2	DTCEN2	00h
008Bh	DTC Activation Enable Register 3	DTCEN3	00h
008Ch			
008Dh	DTC Activation Enable Register 5	DTCEN5	00h
008Eh	DTC Activation Enable Register 6	DTCEN6	00h
008Fh			
0090h			
0091h			
0092h			
0093h			
0094h			
0095h			
0096h			
0097h			
0098h			
0099h			
009Ah			
009Bh			
009Ch			
009Dh			
009Eh			
009Fh			
00A0h	UART0 Transmit/Receive Mode Register	U0MR	00h
00A1h	UART0 Bit Rate Register	U0BRG	XXh
00A2h	UART0 Transmit Buffer Register	U0TB	XXh
00A3h			XXh
00A4h	UART0 Transmit/Receive Control Register 0	U0C0	00001000b
00A5h	UART0 Transmit/Receive Control Register 1	U0C1	00000010b
00A6h	UART0 Receive Buffer Register	U0RB	XXh
00A7h			XXh
00A8h	UART2 Transmit/Receive Mode Register	U2MR	00h
00A9h	UART2 Bit Rate Register	U2BRG	XXh
00AAh	UART2 Transmit Buffer Register	U2TB	XXh
00ABh			XXh
00ACh	UART2 Transmit/Receive Control Register 0	U2C0	00001000b
00ADh	UART2 Transmit/Receive Control Register 1	U2C1	00000010b
00AEh	UART2 Receive Buffer Register	U2RB	XXh
00AFh			XXh
00B0h	UART2 Digital Filter Function Select Register	URXDF	00h
00B1h			
00B2h			
00B3h			
00B4h			
00B5h			
00B6h			
00B7h			
00B8h			
00B9h			
00BAh			
00BBh	UART2 Special Mode Register 5	U2SMR5	00h
00BCh	UART2 Special Mode Register 4	U2SMR4	00h
00BDh	UART2 Special Mode Register 3	U2SMR3	000X0X0Xb
00BEh	UART2 Special Mode Register 2	U2SMR2	X0000000b
00BFh	UART2 Special Mode Register	U2SMR	X0000000b

X: Undefined

Note:

1. The blank areas are reserved and cannot be accessed by users.

Table 4.4 SFR Information (4) ⁽¹⁾

Address	Register	Symbol	After Reset
00C0h	A/D Register 0	AD0	XXh
00C1h			000000XXb
00C2h	A/D Register 1	AD1	XXh
00C3h			000000XXb
00C4h	A/D Register 2	AD2	XXh
00C5h			000000XXb
00C6h	A/D Register 3	AD3	XXh
00C7h			000000XXb
00C8h	A/D Register 4	AD4	XXh
00C9h			000000XXb
00CAh	A/D Register 5	AD5	XXh
00CBh			000000XXb
00CCh	A/D Register 6	AD6	XXh
00CDh			000000XXb
00CEh	A/D Register 7	AD7	XXh
00CFh			000000XXb
00D0h			
00D1h			
00D2h			
00D3h			
00D4h	A/D Mode Register	ADMOD	00h
00D5h	A/D Input Select Register	ADINSEL	11000000b
00D6h	A/D Control Register 0	ADCON0	00h
00D7h	A/D Control Register 1	ADCON1	00h
00D8h	D/A0 Register	DA0	00h
00D9h	D/A1 Register	DA1	00h
00DAh			
00DBh			
00DCh	D/A Control Register	DACON	00h
00DDh			
00DEh			
00DFh			
00E0h	Port P0 Register	P0	XXh
00E1h	Port P1 Register	P1	XXh
00E2h	Port P0 Direction Register	PD0	00h
00E3h	Port P1 Direction Register	PD1	00h
00E4h			
00E5h	Port P3 Register	P3	XXh
00E6h			
00E7h	Port P3 Direction Register	PD3	00h
00E8h	Port P4 Register	P4	XXh
00E9h			
00EAh	Port P4 Direction Register	PD4	00h
00EBh			
00ECh			
00EDh			
00EEh			
00EFh			
00F0h			
00F1h			
00F2h			
00F3h			
00F4h			
00F5h			
00F6h			
00F7h			
00F8h			
00F9h			
00FAh			
00FBh			
00FCh			
00FDh			
00FEh			
00FFh			

X: Undefined

Note:

1. The blank areas are reserved and cannot be accessed by users.

Table 4.11 SFR Information (11) (1)

Address	Register	Symbol	After Reset
2CB0h	DTC Control Data 14	DTCD14	XXh
2CB1h			XXh
2CB2h			XXh
2CB3h			XXh
2CB4h			XXh
2CB5h			XXh
2CB6h			XXh
2CB7h			XXh
2CB8h	DTC Control Data 15	DTCD15	XXh
2CB9h			XXh
2CBAh			XXh
2CBBh			XXh
2CBCh			XXh
2CBDh			XXh
2CBEh			XXh
2CBFh			XXh
2CC0h	DTC Control Data 16	DTCD16	XXh
2CC1h			XXh
2CC2h			XXh
2CC3h			XXh
2CC4h			XXh
2CC5h			XXh
2CC6h			XXh
2CC7h			XXh
2CC8h	DTC Control Data 17	DTCD17	XXh
2CC9h			XXh
2CCAh			XXh
2CCBh			XXh
2CCCh			XXh
2CCDh			XXh
2CCEh			XXh
2CCFh			XXh
2CD0h	DTC Control Data 18	DTCD18	XXh
2CD1h			XXh
2CD2h			XXh
2CD3h			XXh
2CD4h			XXh
2CD5h			XXh
2CD6h			XXh
2CD7h			XXh
2CD8h	DTC Control Data 19	DTCD19	XXh
2CD9h			XXh
2CDAh			XXh
2CDBh			XXh
2CDCh			XXh
2CDDh			XXh
2CDEh			XXh
2CDFh			XXh
2CE0h	DTC Control Data 20	DTCD20	XXh
2CE1h			XXh
2CE2h			XXh
2CE3h			XXh
2CE4h			XXh
2CE5h			XXh
2CE6h			XXh
2CE7h			XXh
2CE8h	DTC Control Data 21	DTCD21	XXh
2CE9h			XXh
2CEAh			XXh
2CEBh			XXh
2CECh			XXh
2CEDh			XXh
2CEEh			XXh
2CEFh			XXh

X: Undefined

Note:

1. The blank areas are reserved and cannot be accessed by users.

5. Electrical Characteristics

Table 5.1 Absolute Maximum Ratings

Symbol	Parameter	Condition	Rated Value	Unit
V _{CC} /AV _{CC}	Supply voltage		−0.3 to 6.5	V
V _I	Input voltage		−0.3 to V _{CC} + 0.3	V
V _O	Output voltage		−0.3 to V _{CC} + 0.3	V
P _d	Power dissipation	−40°C ≤ T _{opr} ≤ 85°C	500	mW
T _{opr}	Operating ambient temperature		−20 to 85 (N version) / −40 to 85 (D version)	°C
T _{stg}	Storage temperature		−65 to 150	°C

Table 5.2 Recommended Operating Conditions

Symbol	Parameter				Conditions	Standard			Unit	
						Min.	Typ.	Max.		
Vcc/AVcc	Supply voltage					1.8	—	5.5	V	
Vss/AVss	Supply voltage					—	0	—	V	
VIH	Input “H” voltage	Other than CMOS input					0.8 Vcc	—	Vcc	V
		CMOS input	Input level switching function (I/O port)	Input level selection: 0.35 Vcc	4.0 V ≤ Vcc ≤ 5.5 V	0.5 Vcc	—	Vcc	V	
					2.7 V ≤ Vcc < 4.0 V	0.55 Vcc	—	Vcc	V	
					1.8 V ≤ Vcc < 2.7 V	0.65 Vcc	—	Vcc	V	
				Input level selection: 0.5 Vcc	4.0 V ≤ Vcc ≤ 5.5 V	0.65 Vcc	—	Vcc	V	
					2.7 V ≤ Vcc < 4.0 V	0.7 Vcc	—	Vcc	V	
					1.8 V ≤ Vcc < 2.7 V	0.8 Vcc	—	Vcc	V	
				Input level selection: 0.7 Vcc	4.0 V ≤ Vcc ≤ 5.5 V	0.85 Vcc	—	Vcc	V	
					2.7 V ≤ Vcc < 4.0 V	0.85 Vcc	—	Vcc	V	
					1.8 V ≤ Vcc < 2.7 V	0.85 Vcc	—	Vcc	V	
	External clock input (XOUT)					1.2	—	Vcc	V	
VIL	Input “L” voltage	Other than CMOS input					0	—	0.2 Vcc	V
		CMOS input	Input level switching function (I/O port)	Input level selection: 0.35 Vcc	4.0 V ≤ Vcc ≤ 5.5 V	0	—	0.2 Vcc	V	
					2.7 V ≤ Vcc < 4.0 V	0	—	0.2 Vcc	V	
					1.8 V ≤ Vcc < 2.7 V	0	—	0.2 Vcc	V	
				Input level selection: 0.5 Vcc	4.0 V ≤ Vcc ≤ 5.5 V	0	—	0.4 Vcc	V	
					2.7 V ≤ Vcc < 4.0 V	0	—	0.3 Vcc	V	
					1.8 V ≤ Vcc < 2.7 V	0	—	0.2 Vcc	V	
				Input level selection: 0.7 Vcc	4.0 V ≤ Vcc ≤ 5.5 V	0	—	0.55 Vcc	V	
					2.7 V ≤ Vcc < 4.0 V	0	—	0.45 Vcc	V	
					1.8 V ≤ Vcc < 2.7 V	0	—	0.35 Vcc	V	
	External clock input (XOUT)					0	—	0.4	V	
IOH(sum)	Peak sum output “H” current	Sum of all pins IOH(peak)				—	—	–160	mA	
IOH(sum)	Average sum output “H” current	Sum of all pins IOH(avg)				—	—	–80	mA	
IOH(peak)	Peak output “H” current	Drive capacity Low				—	—	–10	mA	
		Drive capacity High				—	—	–40	mA	
IOH(avg)	Average output “H” current	Drive capacity Low				—	—	–5	mA	
		Drive capacity High				—	—	–20	mA	
IOL(sum)	Peak sum output “L” current	Sum of all pins IOL(peak)				—	—	160	mA	
IOL(sum)	Average sum output “L” current	Sum of all pins IOL(avg)				—	—	80	mA	
IOL(peak)	Peak output “L” current	Drive capacity Low				—	—	10	mA	
		Drive capacity High				—	—	40	mA	
IOL(avg)	Average output “L” current	Drive capacity Low				—	—	5	mA	
		Drive capacity High				—	—	20	mA	
f(XIN)	XIN clock input oscillation frequency				2.7 V ≤ Vcc ≤ 5.5 V	—	—	20	MHz	
					1.8 V ≤ Vcc < 2.7 V	—	—	5	MHz	
f(XCIN)	XCIN clock input oscillation frequency				1.8 V ≤ Vcc ≤ 5.5 V	—	32.768	50	kHz	
fOCO40M	When used as the count source for timer RC (3)				2.7 V ≤ Vcc ≤ 5.5 V	32	—	40	MHz	
fOCO-F	fOCO-F frequency				2.7 V ≤ Vcc ≤ 5.5 V	—	—	20	MHz	
					1.8 V ≤ Vcc < 2.7 V	—	—	5	MHz	
—	System clock frequency				2.7 V ≤ Vcc ≤ 5.5 V	—	—	20	MHz	
					1.8 V ≤ Vcc < 2.7 V	—	—	5	MHz	
f(BCLK)	CPU clock frequency				2.7 V ≤ Vcc ≤ 5.5 V	—	—	20	MHz	
					1.8 V ≤ Vcc < 2.7 V	—	—	5	MHz	

Notes:

1. V_{CC} = 1.8 to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. The average output current indicates the average value of current measured during 100 ms.
3. f_{OCO40M} can be used as the count source for timer RC in the range of V_{CC} = 2.7 V to 5.5V.

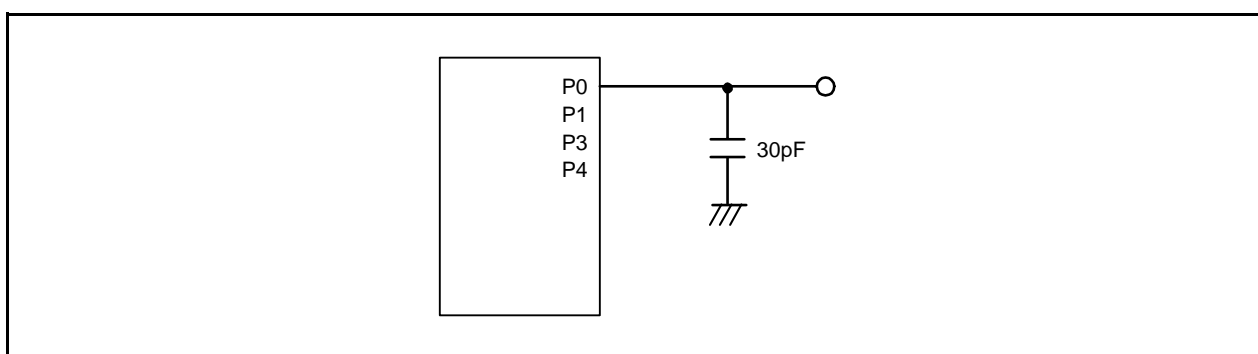


Figure 5.1 Ports P0 to P1, P3 to P4 Timing Measurement Circuit

Table 5.3 A/D Converter Characteristics

Symbol	Parameter		Conditions		Standard			Unit
					Min.	Typ.	Max.	
–	Resolution		V _{ref} = AV _{CC}		–	–	10	Bit
–	Absolute accuracy	10-bit mode	V _{ref} = AV _{CC} = 5.0 V	AN0, AN1, AN5, AN6 input, AN8 to AN11 input	–	–	±3	LSB
			V _{ref} = AV _{CC} = 3.3 V	AN0, AN1, AN5, AN6 input, AN8 to AN11 input	–	–	±5	LSB
			V _{ref} = AV _{CC} = 3.0 V	AN0, AN1, AN5, AN6 input, AN8 to AN11 input	–	–	±5	LSB
			V _{ref} = AV _{CC} = 2.2 V	AN0, AN1, AN5, AN6 input, AN8 to AN11 input	–	–	±5	LSB
		8-bit mode	V _{ref} = AV _{CC} = 5.0 V	AN0, AN1, AN5, AN6 input, AN8 to AN11 input	–	–	±2	LSB
			V _{ref} = AV _{CC} = 3.3 V	AN0, AN1, AN5, AN6 input, AN8 to AN11 input	–	–	±2	LSB
			V _{ref} = AV _{CC} = 3.0 V	AN0, AN1, AN5, AN6 input, AN8 to AN11 input	–	–	±2	LSB
			V _{ref} = AV _{CC} = 2.2 V	AN0, AN1, AN5, AN6 input, AN8 to AN11 input	–	–	±2	LSB
φAD	A/D conversion clock		4.0 V ≤ V _{ref} = AV _{CC} ≤ 5.5 V ⁽²⁾		2	–	20	MHz
			3.2 V ≤ V _{ref} = AV _{CC} ≤ 5.5 V ⁽²⁾		2	–	16	MHz
			2.7 V ≤ V _{ref} = AV _{CC} ≤ 5.5 V ⁽²⁾		2	–	10	MHz
			2.2 V ≤ V _{ref} = AV _{CC} ≤ 5.5 V ⁽²⁾		2	–	5	MHz
–	Tolerance level impedance				–	3	–	kΩ
tCONV	Conversion time	10-bit mode	V _{ref} = AV _{CC} = 5.0 V, φAD = 20 MHz		2.2	–	–	μs
		8-bit mode	V _{ref} = AV _{CC} = 5.0 V, φAD = 20 MHz		2.2	–	–	μs
tsAMP	Sampling time		φAD = 20 MHz		0.8	–	–	μs
I _{Vref}	V _{ref} current		V _{CC} = 5 V, XIN = f1 = φAD = 20 MHz		–	45	–	μA
V _{ref}	Reference voltage				2.2	–	AV _{CC}	V
V _{IA}	Analog input voltage ⁽³⁾				0	–	V _{ref}	V
OCVREF	On-chip reference voltage		2 MHz ≤ φAD ≤ 4 MHz		1.19	1.34	1.49	V

Notes:

1. $V_{CC}/AV_{CC} = V_{ref} = 2.2$ to 5.5 V , $V_{SS} = 0\text{ V}$ and $T_{opr} = -20$ to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. The A/D conversion result will be undefined in wait mode, stop mode, when the flash memory stops, and in low-current-consumption mode. Do not perform A/D conversion in these states or transition to these states during A/D conversion.
3. When the analog input voltage is over the reference voltage, the A/D conversion result will be 3FFh in 10-bit mode and FFh in 8-bit mode.

Table 5.7 Flash Memory (Data flash Block A to Block D) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance ⁽²⁾		10,000 ⁽³⁾	–	–	times
–	Byte program time (program/erase endurance ≤ 1,000 times)		–	160	1,500	μs
–	Byte program time (program/erase endurance > 1,000 times)		–	300	1,500	μs
–	Block erase time (program/erase endurance ≤ 1,000 times)		–	0.2	1	s
–	Block erase time (program/erase endurance > 1,000 times)		–	0.3	1	s
t _d (SR-SUS)	Time delay from suspend request until suspend		–	–	5+CPU clock × 3 cycles	ms
–	Interval from erase start/restart until following suspend request		0	–	–	μs
–	Time from suspend until erase restart		–	–	30+CPU clock × 1 cycle	μs
t _d (CMDRST-READY)	Time from when command is forcibly terminated until reading is enabled		–	–	30+CPU clock × 1 cycle	μs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		1.8	–	5.5	V
–	Program, erase temperature		–20 ⁽⁷⁾	–	85	°C
–	Data hold time ⁽⁸⁾	Ambient temperature = 55 °C	20	–	–	year

Notes:

1. V_{CC} = 2.7 to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. Definition of programming/erasure endurance
The programming and erasure endurance is defined on a per-block basis.
If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A to D can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. –40°C for D version.
8. The data hold time includes time that the power supply is off or the clock is not supplied.

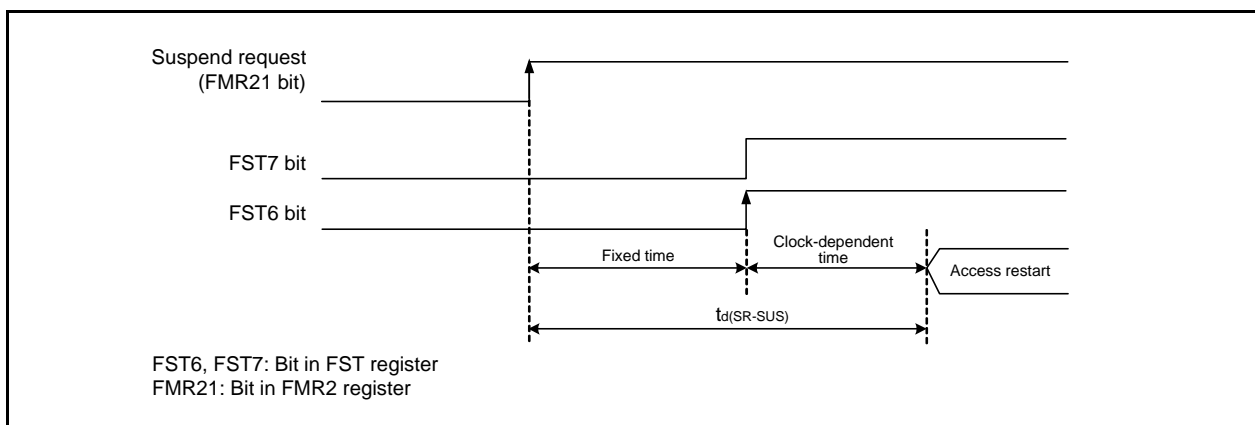
**Figure 5.2 Time delay until Suspend**

Table 5.8 Voltage Detection 0 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V _{det0}	Voltage detection level V _{det0_0} (2)		1.80	1.90	2.05	V
	Voltage detection level V _{det0_1} (2)		2.15	2.35	2.50	V
	Voltage detection level V _{det0_2} (2)		2.70	2.85	3.05	V
	Voltage detection level V _{det0_3} (2)		3.55	3.80	4.05	V
—	Voltage detection 0 circuit response time (4)	At the falling of V _{CC} from 5 V to (V _{det0_0} – 0.1) V	—	6	150	μs
—	Voltage detection circuit self power consumption	VCA25 = 1, V _{CC} = 5.0 V	—	1.5	—	μA
t _{d(E-A)}	Waiting time until voltage detection circuit operation starts (3)		—	—	100	μs

Notes:

1. The measurement condition is V_{CC} = 1.8 V to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version).
2. Select the voltage detection level with bits VDSEL0 and VDSEL1 in the OFS register.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA25 bit in the VCA2 register to 0.
4. Time until the voltage monitor 0 reset is generated after the voltage passes V_{det0}.

Table 5.9 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V _{det1}	Voltage detection level V _{det1_0} (2)	At the falling of V _{CC}	2.00	2.20	2.40	V
	Voltage detection level V _{det1_1} (2)	At the falling of V _{CC}	2.15	2.35	2.55	V
	Voltage detection level V _{det1_2} (2)	At the falling of V _{CC}	2.30	2.50	2.70	V
	Voltage detection level V _{det1_3} (2)	At the falling of V _{CC}	2.45	2.65	2.85	V
	Voltage detection level V _{det1_4} (2)	At the falling of V _{CC}	2.60	2.80	3.00	V
	Voltage detection level V _{det1_5} (2)	At the falling of V _{CC}	2.75	2.95	3.15	V
	Voltage detection level V _{det1_6} (2)	At the falling of V _{CC}	2.85	3.10	3.40	V
	Voltage detection level V _{det1_7} (2)	At the falling of V _{CC}	3.00	3.25	3.55	V
	Voltage detection level V _{det1_8} (2)	At the falling of V _{CC}	3.15	3.40	3.70	V
	Voltage detection level V _{det1_9} (2)	At the falling of V _{CC}	3.30	3.55	3.85	V
	Voltage detection level V _{det1_A} (2)	At the falling of V _{CC}	3.45	3.70	4.00	V
	Voltage detection level V _{det1_B} (2)	At the falling of V _{CC}	3.60	3.85	4.15	V
	Voltage detection level V _{det1_C} (2)	At the falling of V _{CC}	3.75	4.00	4.30	V
	Voltage detection level V _{det1_D} (2)	At the falling of V _{CC}	3.90	4.15	4.45	V
	Voltage detection level V _{det1_E} (2)	At the falling of V _{CC}	4.05	4.30	4.60	V
	Voltage detection level V _{det1_F} (2)	At the falling of V _{CC}	4.20	4.45	4.75	V
—	Hysteresis width at the rising of V _{CC} in voltage detection 1 circuit	V _{det1_0} to V _{det1_5} selected	—	0.07	—	V
		V _{det1_6} to V _{det1_F} selected	—	0.10	—	V
—	Voltage detection 1 circuit response time (3)	At the falling of V _{CC} from 5 V to (V _{det1_0} – 0.1) V	—	60	150	μs
—	Voltage detection circuit self power consumption	VCA26 = 1, V _{CC} = 5.0 V	—	1.7	—	μA
t _{d(E-A)}	Waiting time until voltage detection circuit operation starts (4)		—	—	100	μs

Notes:

1. The measurement condition is V_{CC} = 1.8 V to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version).
2. Select the voltage detection level with bits VD1S0 to VD1S3 in the VD1LS register.
3. Time until the voltage monitor 1 interrupt request is generated after the voltage passes V_{det1}.
4. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.

**Table 5.12 High-speed On-Chip Oscillator Circuit Electrical Characteristics
(Package Type: PWQN0024KC-A)**

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
—	High-speed on-chip oscillator frequency after reset	$V_{CC} = 1.8 \text{ V to } 5.5 \text{ V}$ $-20^{\circ}\text{C} \leq T_{opr} \leq 85^{\circ}\text{C}$	37.80	40	42.60	MHz
	High-speed on-chip oscillator frequency when the FRA4 register correction value is written into the FRA1 register and the FRA5 register correction value into the FRA3 register ⁽²⁾	$V_{CC} = 1.8 \text{ V to } 5.5 \text{ V}$ $-20^{\circ}\text{C} \leq T_{opr} \leq 85^{\circ}\text{C}$	34.836	36.864	39.261	MHz
	High-speed on-chip oscillator frequency when the FRA6 register correction value is written into the FRA1 register and the FRA7 register correction value into the FRA3 register	$V_{CC} = 1.8 \text{ V to } 5.5 \text{ V}$ $-20^{\circ}\text{C} \leq T_{opr} \leq 85^{\circ}\text{C}$	30.24	32	34.08	MHz
—	Oscillation stability time	$V_{CC} = 5.0 \text{ V}$, $T_{opr} = 25^{\circ}\text{C}$	—	0.5	3	ms
—	Self power consumption at oscillation	$V_{CC} = 5.0 \text{ V}$, $T_{opr} = 25^{\circ}\text{C}$	—	400	—	μA

Notes:

1. $V_{CC} = 1.8$ to 5.5 V , $T_{opr} = -20$ to 85°C (N version), unless otherwise specified.
2. This enables the setting errors of bit rates such as 9600 bps and 38400 bps to be 0% when the serial interface is used in UART mode.

**Table 5.13 High-speed On-Chip Oscillator Circuit Electrical Characteristics
(Package Type: PLSP0024JB-A)**

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
—	High-speed on-chip oscillator frequency after reset	$V_{CC} = 1.8 \text{ V to } 5.5 \text{ V}$ $-20^{\circ}\text{C} \leq T_{opr} \leq 85^{\circ}\text{C}$	38.4	40	41.6	MHz
		$V_{CC} = 1.8 \text{ V to } 5.5 \text{ V}$ $-40^{\circ}\text{C} \leq T_{opr} \leq 85^{\circ}\text{C}$	38.0	40	42.0	MHz
	High-speed on-chip oscillator frequency when the FRA4 register correction value is written into the FRA1 register and the FRA5 register correction value into the FRA3 register ⁽²⁾	$V_{CC} = 1.8 \text{ V to } 5.5 \text{ V}$ $-20^{\circ}\text{C} \leq T_{opr} \leq 85^{\circ}\text{C}$	35.389	36.864	38.338	MHz
		$V_{CC} = 1.8 \text{ V to } 5.5 \text{ V}$ $-40^{\circ}\text{C} \leq T_{opr} \leq 85^{\circ}\text{C}$	35.020	36.864	38.707	MHz
	High-speed on-chip oscillator frequency when the FRA6 register correction value is written into the FRA1 register and the FRA7 register correction value into the FRA3 register	$V_{CC} = 1.8 \text{ V to } 5.5 \text{ V}$ $-20^{\circ}\text{C} \leq T_{opr} \leq 85^{\circ}\text{C}$	30.72	32	33.28	MHz
		$V_{CC} = 1.8 \text{ V to } 5.5 \text{ V}$ $-40^{\circ}\text{C} \leq T_{opr} \leq 85^{\circ}\text{C}$	30.40	32	33.60	MHz
—	Oscillation stability time	$V_{CC} = 5.0 \text{ V}$, $T_{opr} = 25^{\circ}\text{C}$	—	0.5	3	ms
—	Self power consumption at oscillation	$V_{CC} = 5.0 \text{ V}$, $T_{opr} = 25^{\circ}\text{C}$	—	400	—	μA

Notes:

1. $V_{CC} = 1.8$ to 5.5 V , $T_{opr} = -20$ to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. This enables the setting errors of bit rates such as 9600 bps and 38400 bps to be 0% when the serial interface is used in UART mode.

Table 5.14 Low-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO-S	Low-speed on-chip oscillator frequency		60	125	250	kHz
—	Oscillation stability time	$V_{CC} = 5.0 \text{ V}$, $T_{opr} = 25^{\circ}\text{C}$	—	30	100	μs
—	Self power consumption at oscillation	$V_{CC} = 5.0 \text{ V}$, $T_{opr} = 25^{\circ}\text{C}$	—	2	—	μA

Note:

1. $V_{CC} = 1.8$ to 5.5 V , $T_{opr} = -20$ to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.

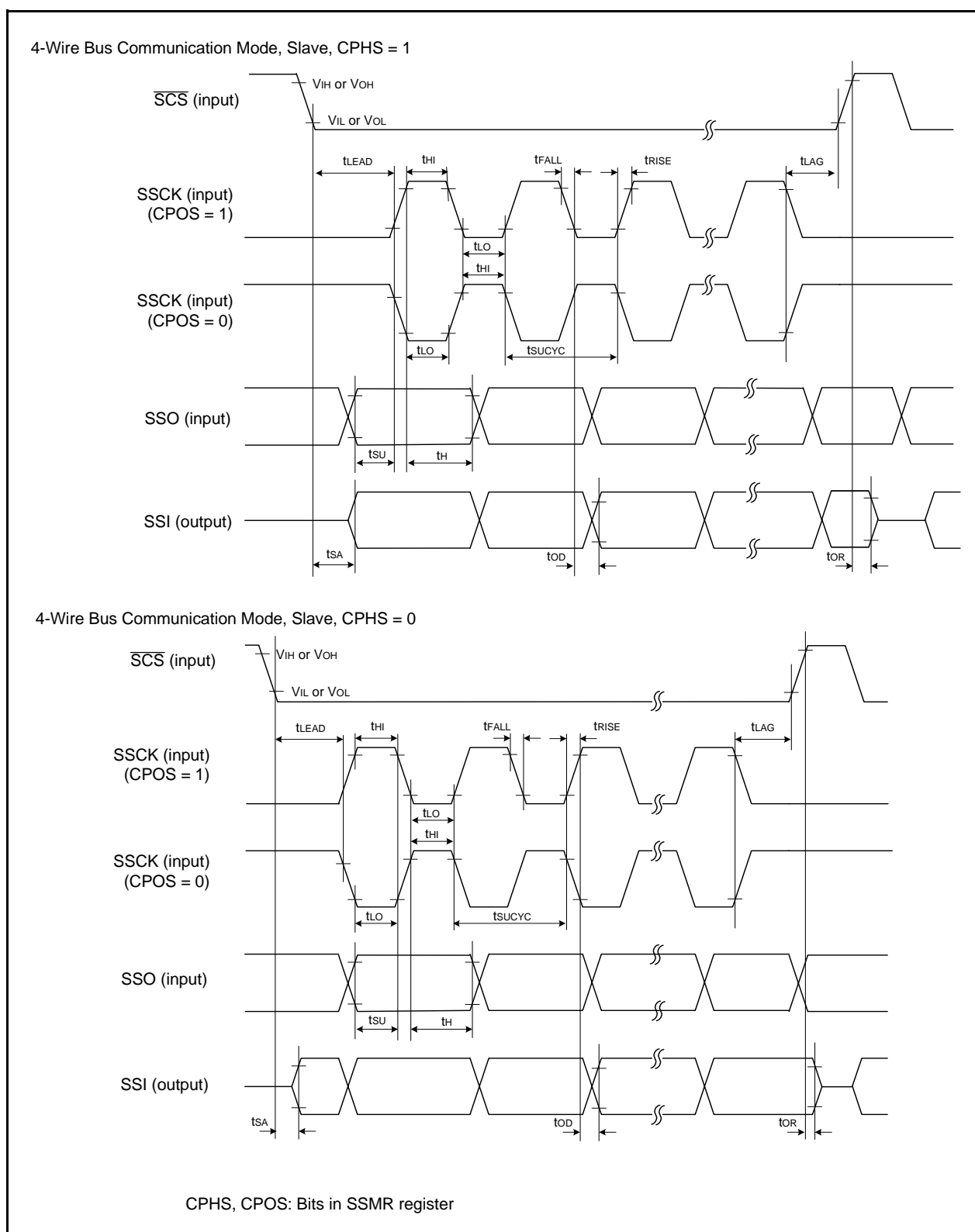
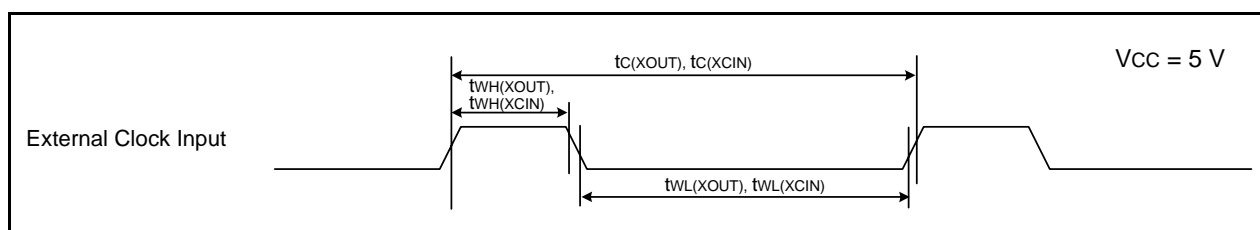


Figure 5.5 I/O Timing of Synchronous Serial Communication Unit (SSU) (Slave)

Timing Requirements**(Unless Otherwise Specified: $V_{CC} = 5\text{ V}$, $V_{SS} = 0\text{ V}$ at $T_{opr} = 25^\circ\text{C}$)****Table 5.20 External Clock Input (XOUT, XCIN)**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XOUT)}$	XOUT input cycle time	50	–	ns
$t_{WH(XOUT)}$	XOUT input “H” width	24	–	ns
$t_{WL(XOUT)}$	XOUT input “L” width	24	–	ns
$t_{c(XCIN)}$	XCIN input cycle time	14	–	μs
$t_{WH(XCIN)}$	XCIN input “H” width	7	–	μs
$t_{WL(XCIN)}$	XCIN input “L” width	7	–	μs

**Figure 5.8 External Clock Input Timing Diagram when $V_{CC} = 5\text{ V}$** **Table 5.21 TRAIO Input**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	100	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	40	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	40	–	ns

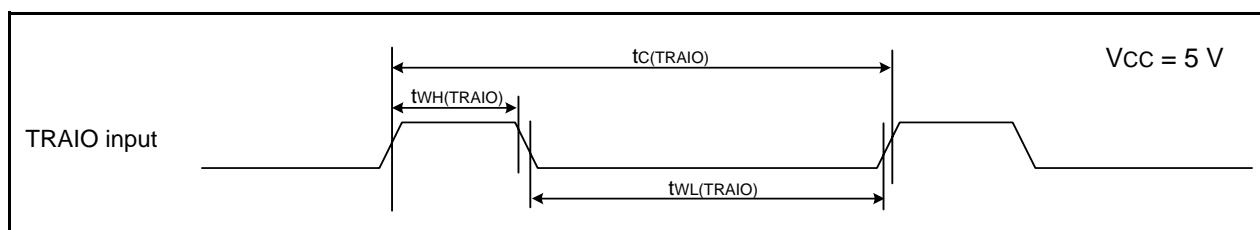
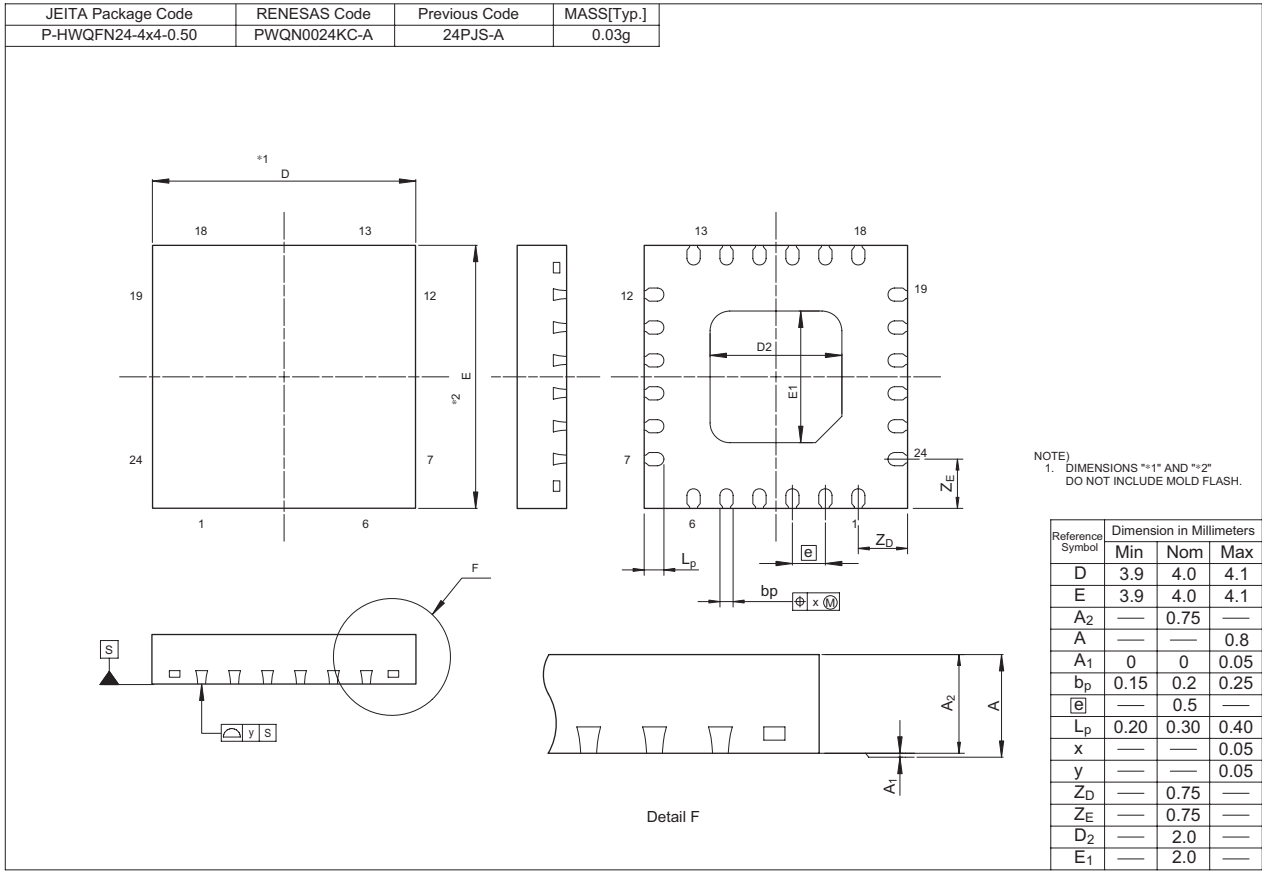
**Figure 5.9 TRAIO Input Timing Diagram when $V_{CC} = 5\text{ V}$**

Table 5.31 Electrical Characteristics (6) [$1.8\text{ V} \leq V_{CC} < 2.7\text{ V}$]
($T_{opr} = -20\text{ to }85^{\circ}\text{C}$ (N version) / $-40\text{ to }85^{\circ}\text{C}$ (D version), unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
I _{CC}	Power supply current ($V_{CC} = 1.8\text{ to }2.7\text{ V}$) Single-chip mode, output pins are open, other pins are V _{SS}	High-speed clock mode	XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division			mA
			XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8			mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO-F = 5 MHz Low-speed on-chip oscillator on = 125 kHz No division			mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 5 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8			mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16 MSTIIC = MSTTRD = MSTTRC = 1			mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0			μA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division, FMR27 = 1, VCA20 = 0			μA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division, Program operation on RAM Flash memory off, FMSTP = 1, VCA20 = 0			μA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1			μA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1			μA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (peripheral clock off) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1			μA
		Stop mode	XIN clock off, $T_{opr} = 25^{\circ}\text{C}$ High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0			μA
			XIN clock off, $T_{opr} = 85^{\circ}\text{C}$ High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0			μA

Package Dimensions

Diagrams showing the latest package dimensions and mounting information are available in the “Packages” section of the Renesas Electronics website.



General Precautions in the Handling of MPU/MCU Products

The following usage notes are applicable to all MPU/MCU products from Renesas. For detailed usage notes on the products covered by this manual, refer to the relevant sections of the manual. If the descriptions under General Precautions in the Handling of MPU/MCU Products and in the body of the manual differ from each other, the description in the body of the manual takes precedence.

1. Handling of Unused Pins

Handle unused pins in accord with the directions given under Handling of Unused Pins in the manual.

- The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible. Unused pins should be handled as described under Handling of Unused Pins in the manual.

2. Processing at Power-on

The state of the product is undefined at the moment when power is supplied.

- The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the moment when power is supplied.

In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the moment when power is supplied until the reset process is completed.

In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the moment when power is supplied until the power reaches the level at which resetting has been specified.

3. Prohibition of Access to Reserved Addresses

Access to reserved addresses is prohibited.

- The reserved addresses are provided for the possible future expansion of functions. Do not access these addresses; the correct operation of LSI is not guaranteed if they are accessed.

4. Clock Signals

After applying a reset, only release the reset line after the operating clock signal has become stable. When switching the clock signal during program execution, wait until the target clock signal has stabilized.

- When the clock signal is generated with an external resonator (or from an external oscillator) during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Moreover, when switching to a clock signal produced with an external resonator (or by an external oscillator) while program execution is in progress, wait until the target clock signal is stable.

5. Differences between Products

Before changing from one product to another, i.e. to one with a different part number, confirm that the change will not lead to problems.

- The characteristics of MPU/MCU in the same group but having different part numbers may differ because of the differences in internal memory capacity and layout pattern. When changing to products of different part numbers, implement a system-evaluation test for each of the products.